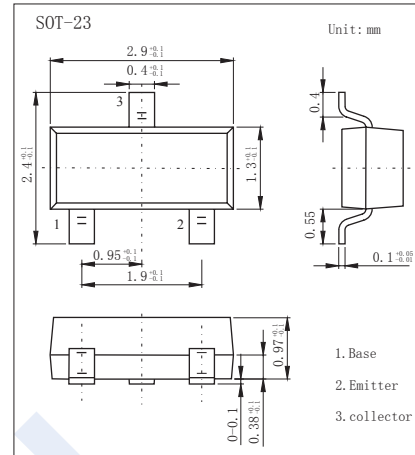


NPN Transistors

2SC3265

■ Features

- High DC current gain
- Low saturation voltage
- Complementary to 2SA1298

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	30	V
Collector - Emitter Voltage	V_{CE0}	25	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	800	mA
Base Current	I_B	160	
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = 100\ \mu\text{A}$, $I_E = 0$	30			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 10\ \text{mA}$, $I_B = 0$	25			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100\ \mu\text{A}$, $I_C = 0$	5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 30\ \text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5\ \text{V}$, $I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\ \text{mA}$, $I_B = 20\ \text{mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\ \text{mA}$, $I_B = 20\ \text{mA}$		0.72	1	
Base - emitter voltage	V_{BE}	$V_{CE} = 1\ \text{V}$, $I_C = 10\ \text{mA}$	0.5		0.8	
DC current gain	h_{FE}	$V_{CE} = 1\ \text{V}$, $I_C = 100\ \text{mA}$	100		320	
		$V_{CE} = 1\ \text{V}$, $I_C = 800\ \text{mA}$	40			
Collector output capacitance	C_{ob}	$V_{CB} = 10\ \text{V}$, $I_E = 0$, $f = 1\ \text{MHz}$		13		pF
Transition frequency	f_T	$V_{CE} = 5\ \text{V}$, $I_C = 10\ \text{mA}$		120		MHz

■ Classification of $h_{FE}(1)$

Marking	EO	EY
Range	100-200	160-320

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■ Typical Characteristics

